

ABSTRACT OF THE INVENTION

The present invention relates to a method of anisotropically etching a semiconductive substrate uses a hydrofluorocarbon etch gas with an etch selectivity fluorocarbon gas that previously was used to enhance oxide etching but not nitride selectivity. The present invention uses the fluorocarbon gas under conditions that enhance selectivity of the etch to nitride with respect to a bulk dielectric material such as doped and undoped silicon dioxide.

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